



SHEET 1 OF 1

INFORMATION DISCLOSURE CITATION IN AN APPLICATION  (PTO-1449)				ATTY. DOCKET NO. <b>057454-0979</b>		SERIAL NO. <b>10/691,513</b>	
				APPLICANT <b>Hideto HIDAKA</b>			
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<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code <sup>2</sup> (if known)		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
TL		US	2002/0009003 A1	01/24/2002	Hartmann	Corresponds to DE 100 34062 A1	
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EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Code <sup>1</sup> -Number 4-Kind Codes (if known)		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation Yes No
TL		WO 99/53499		10/21/1999	HONEYWELL, INC		X
TL		EP 1 132 924 A2		10/11/2000	HEWLETT-PACKARD COMPANY, A DELAWARE CORPORATION		X
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<b>OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
TL		Scheuerlein, R., et al. "A 10ns read and write non-volatile memory array using a magnetic tunnel junction and FET switch in each cell" IEEE International Solid-State Circuits Conference, February 7-9, 2000, pp 128-129.					
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EXAMINER <i>Hoyle</i>				DATE CONSIDERED <i>12/7/05</i>			

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.